


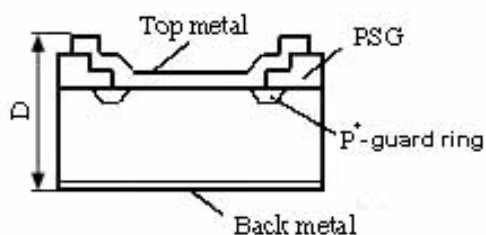
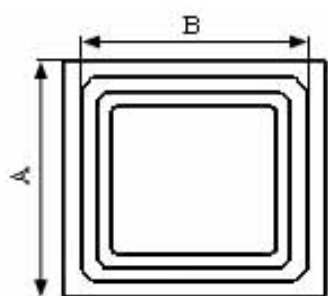
# SCHOTTKY DIODES KDN-10020.

PRELIMINARY



Rev.1. Feb. 2010

 <b>VSP-MIKRON</b>		<b>10A/20V. Die Size-90mil.</b>		
Electrical Characteristics	Symbol	Unit	Spec. limit	Die Sort
Breakdown Voltage @ $I_R=10mA$	$V_{BR}$	V	20	25
Average Rectified Forward Current	$I_{F(AV)}$	A	10,0	-
DC Forward Voltage @ 25°C, $I_F=10,0A$	$V_F$	V	0,50	0,48
Maximum Reverse Current @ 25°C, $V_R=25V$ 25°C, $V_R=20V$ 125°C, $V_R=20V$	$I_R$	mA	- 0,250 110,0	0,250 0,180 100,0
Peak Forward Surge Current 8,3ms single half sine-wave superimposed on rated load (JEDEC METHOD)	$I_{FSM}$	A	150	-
Peak Repetitive Reverse Surge Current @2,0µs, f=1kHz., $T_J<150°C$ .	$I_{RRM}$	A	3,5	
Electrostatic Discharge Voltage. JEDEC Method. ESD HBM. Contact.	ESD	kV	±8 (contact)	
Voltage Rate of Change	dV/dt	V/µS	10.000	
Operating Junction Temperature	$T_J$	°C	150	



DIM	ITEM	µm
$A_x$ $A_y$	Wafer Form Die Size	2280 2280
$B_x$ $B_y$	Top Metal Size	2140 2140
D	Thickness	350max.
Scribe line Width		80

Top metal: a) **Al** – for Wire Bonding;  
b) **Al-Ni-Ag**; - for Soldering.  
Backside metal: **Ti-Ni-Ag**.